

Title (en)

SOI CONTACT STRUCTURE(S) AND CORRESPONDING PRODUCTION METHOD

Title (de)

SOI KONTAKTSTRUKTUR(EN) UND ZUGEHÖRIGES HERSTELLUNGSVERFAHREN

Title (fr)

STRUCTURE(S) DE CONTACT DE TYPE SILICIUM SUR ISOLANT (SOI) ET PROCEDE DE PRODUCTION CORRESPONDANT

Publication

EP 1595285 A1 20051116 (DE)

Application

EP 04706605 A 20040130

Priority

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Abstract (en)

[origin: WO2004068574A1] Disclosed are an arrangement and a production method for electrically connecting active semiconductor structures in or on a monocrystalline silicon layer (12) located on the front face (V) of silicon-on-insulator semiconductor wafers (SOI, 10) to the substrate (13). The electrical connection (20) is made through an insulator layer (11). A stack of layers (30 to 32, 70 to 72) is disposed above the connection piece (20) on the insulator layer (11).

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H01L 21/74

IPC 8 full level

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CPC (source: EP US)

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